

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor device comprising:
an active layer comprising a semiconductor film comprising silicon;
a gate electrode comprising tantalum adjacent to said active layer with a gate insulating film interposed therebetween;
an inorganic film over said active layer and on said gate electrode; and
a resin film over said inorganic film,
wherein a concentration of nickel in a source region and a drain region formed in said active layer is higher than a concentration of nickel in other regions in said active layer by two or more orders of magnitude, and
wherein said source region and said drain region comprise a nickel phosphide.
2. (Previously Presented) The semiconductor device according to claim 1, wherein said nickel phosphide is one of NiP, NiP₂ and Ni₂P.
- 3.-4. (Canceled)
5. (Previously Presented) The semiconductor device according to claim 1, wherein said semiconductor device is one selected from the group consisting of a portable intelligent terminal, a head mounted display, a front-projection type liquid crystal display, a cellular mobile telephone, a portable video camera, and a rear-projection liquid crystal display.
6. (Canceled)

7. (Previously Presented) The semiconductor device according to claim 1, wherein said gate electrode has a heat-resistance to a heat treatment of 700°C.

8.-34. (Canceled)

35. (Previously Presented) A semiconductor device comprising:
an active layer comprising a semiconductor film comprising silicon;
a gate electrode comprising tantalum adjacent to said active layer with a gate insulating film interposed therebetween;
a film comprising silicon and nitride over said active layer and on said gate electrode; and
a resin film over said film comprising silicon and nitride,
wherein a concentration of nickel in a source region and a drain region formed in said active layer is higher than a concentration of nickel in other regions in said active layer by two or more orders of magnitude, and
wherein said source region and said drain region comprise a nickel phosphide.

36. (Previously Presented) The semiconductor device according to claim 35, wherein said nickel phosphide is one of NiP, NiP₂ and Ni₂P.

37. (Canceled)

38. (Previously Presented) The semiconductor device according to claim 35, wherein said gate electrode has a heat-resistance to a heat treatment of 700°C.

39. (Previously Presented) The semiconductor device according to claim 35, wherein said semiconductor device is one selected from the group consisting of a

portable intelligent terminal, a head mounted display, a front-projection type liquid crystal display, a cellular mobile telephone, a portable video camera, and a rear-projection liquid crystal display.

40. (Previously Presented) The semiconductor device according to claim 1, wherein said resin film comprises a material selected from the group consisting of acrylics, polyimide, polyamide, polyimideamide, and epoxies.

41. (Previously Presented) The semiconductor device according to claim 35, wherein said resin film comprises a material selected from the group consisting of acrylics, polyimide, polyamide, polyimideamide, and epoxies.

42. (Previously Presented) A semiconductor device comprising:
an active layer comprising a semiconductor film comprising silicon;
a gate electrode comprising tantalum adjacent to said active layer with a gate insulating film interposed therebetween;
an inorganic film over said active layer and on said gate electrode; and
a resin film over said inorganic film,
wherein a concentration of nickel in a source region and a drain region formed in said active layer is higher than a concentration of nickel in other regions in said active layer which is less than 5×10^{16} atoms/cm³, and
wherein said source region and said drain region comprise a nickel phosphide.

43. (Previously Presented) The semiconductor device according to claim 42, wherein said nickel phosphide is one of NiP, NiP₂ and Ni₂P.

44. (Canceled)

45. (Previously Presented) The semiconductor device according to claim 42, wherein said gate electrode has a heat-resistance to a heat treatment of 700°C.

46. (Previously Presented) The semiconductor device according to claim 42, wherein said semiconductor device is one selected from the group consisting of a portable intelligent terminal, a head mounted display, a front-projection type liquid crystal display, a cellular mobile telephone, a portable video camera, and a rear-projection liquid crystal display.

47. (Previously Presented) A semiconductor device comprising:
an active layer comprising a semiconductor film comprising silicon;
a gate electrode comprising a heat-resistant material adjacent to said active layer with a gate insulating film interposed therebetween;
a film comprising silicon and nitride over said active layer and on said gate electrode; and
a resin film over said film comprising silicon and nitride,
wherein a concentration of nickel in a source region and a drain region formed in said active layer is higher than a concentration of nickel in other regions in said active layer which is less than 5×10^{16} atoms/cm³, and
wherein said source region and said drain region comprise a nickel phosphide.

48. (Previously Presented) The semiconductor device according to claim 47, wherein said nickel phosphide is one of NiP, NiP₂ and Ni₂P.

49. (Canceled)

50. (Previously Presented) The semiconductor device according to claim 47, wherein said gate electrode has a heat-resistance to a heat treatment of 700°C.

51. (Previously Presented) The semiconductor device according to claim 47, wherein said semiconductor device is one selected from the group consisting of a portable intelligent terminal, a head mounted display, a front-projection type liquid crystal display, a cellular mobile telephone, a portable video camera, and a rear-projection liquid crystal display.

52. (Previously Presented) The semiconductor device according to claim 42, wherein said resin film comprises a material selected from the group consisting of acrylics, polyimide, polyamide, polyimideamide, and epoxies.

53. (Previously Presented) The semiconductor device according to claim 47, wherein said resin film comprises a material selected from the group consisting of acrylics, polyimide, polyamide, polyimideamide, and epoxies.

54. (Previously Presented) A semiconductor device comprising:
an active layer comprising a semiconductor film comprising silicon;
a gate electrode comprising tantalum adjacent to said active layer with a gate insulating film interposed therebetween;
an inorganic film over said active layer and on said gate electrode; and
a resin film over said inorganic film,
wherein a source region and a drain region formed in said active layer comprise a nickel phosphide.

55. (Previously Presented) The semiconductor device according to claim 54, wherein said nickel phosphide is one of NiP, NiP₂ and Ni₂P.

56. (Previously Presented) The semiconductor device according to claim 54, wherein said gate electrode has a heat-resistance to a heat treatment of 700°C.

57. (Previously Presented) The semiconductor device according to claim 54, wherein said semiconductor device is one selected from the group consisting of a portable intelligent terminal, a head mounted display, a front-projection type liquid crystal display, a cellular mobile telephone, a portable video camera, and a rear-projection liquid crystal display.

58. (Previously Presented) A semiconductor device comprising:
an active layer comprising a semiconductor film comprising silicon;
a gate electrode comprising tantalum adjacent to said active layer with a gate insulating film interposed therebetween;
a film comprising silicon and nitride over said active layer and on said gate electrode; and
a resin film over said film comprising silicon and nitride,
wherein a source region and a drain region formed in said active layer comprise a nickel phosphide.

59. (Previously Presented) The semiconductor device according to claim 58, wherein said nickel phosphide is one of NiP, NiP₂ and Ni₂P.

60. (Previously Presented) The semiconductor device according to claim 58, wherein said gate electrode has a heat-resistance to a heat treatment of 700°C.

61. (Previously Presented) The semiconductor device according to claim 58, wherein said semiconductor device is one selected from the group consisting of a portable intelligent terminal, a head mounted display, a front-projection type liquid

crystal display, a cellular mobile telephone, a portable video camera, and a rear-projection liquid crystal display.

62.-73. (Canceled)

74. (Previously Presented) The semiconductor device according to claim 54, wherein said resin film comprises a material selected from the group consisting of acrylics, polyimide, polyamide, polyimideamide, and epoxies.

75. (Previously Presented) The semiconductor device according to claim 58, wherein said resin film comprises a material selected from the group consisting of acrylics, polyimide, polyamide, polyimideamide, and epoxies.

76.-105. (Canceled)